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Titolo	Next generation mobile broadcasting / / edited by David Gomez-Barquero
Pubbl/distr/stampa	Boca Raton : , : Taylor & Francis, , 2013
ISBN	0-429-06754-2 1-4398-9869-3
Descrizione fisica	1 online resource (793 p.)
Classificazione	TEC061000
Altri autori (Persone)	Gomez-BarqueroDavid
Disciplina	621.388/5
Soggetti	Mobile television Mobile computing Multimedia communications
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references.
Nota di contenuto	Front Cover; Contents; List of Institutions; List of Figures; Editor; Contributors; Chapter 1 - Next-Generation Mobile Multimedia Broadcasting; Chapter 2 - An Overview of the ISDB-T One-Seg Broadcasting, ISDB-TSB and ISDB-Tmm; Chapter 3 - Overview of the South Korean Advanced T-DMB Mobile Broadcasting System; Chapter 4 - An Overview of the North American ATSC M/H Mobile Broadcasting System and Its Next-Generation ATSC 3.0; Chapter 5 - Overview of the Chinese Digital Terrestrial Multimedia Broadcasting System; Chapter 6 - DVB-T2 for Mobile and Mobile DVB-T2 (T2-Lite) Chapter 7 - An Overview of the Next-Generation Mobile Digital Video Broadcasting Standard DVB-NGHChapter 8 - An Overview of the Cellular Broadcasting Technology eMBMS in LTE; Chapter 9 - Universal DVB-3GPP Broadcast Layer: An Enabler for New Business in Mobile Broadcasting Landscape; Chapter 10 - Overview of the HEVC Video Coding Standard; Chapter 11 - Bit-Interleaved Coded Modulation in Next-Generation Mobile Broadcast Standard DVB-NGH; Chapter 12 - Time Interleaving in DVB-NGH; Chapter 13 - Time-Frequency Slicing for DVB-NGH Chapter 14 - DVB-NGH Logical Frame Structure and Bundling DVB-T2 Future Extension FramesChapter 15 - Overview of the Physical Layer Signaling in DVB-NGH; Chapter 16 - Overview of the System and Upper

	Layers of DVB-NGH; Chapter 17 - Overhead Reduction Methods in DVB-NGH; Chapter 18 - Local Service Insertion in DVB-NGH Single-Frequency Networks; Chapter 19 - Overview of the Multiple-Input Multiple-Output Terrestrial Profile of DVB-NGH; Chapter 20 - Multiple-Input Single-Output Antenna Schemes for DVB-NGH; Chapter 21 - Enhanced MIMO Spatial Multiplexing with Phase Hopping for DVB-NGH Chapter 22 - An Overview of the Hybrid Terrestrial-Satellite Profile of DVB-NGHChapter 23 - Single-Carrier OFDM for the Satellite Component of DVB-NGH; Chapter 24 - Hybrid Satellite-Terrestrial MIMO for Mobile Digital Broadcasting; Back Cover
Sommario/riassunto	Edited by a member of the DVB-NGH standardization meeting, this book covers the newest finalized standards. The first section contains overview papers, including commercial requirements and limitations of DVB-T2. It covers the first version of the standard, very aligned to T2, called T2+M, and a second version with the new technical features of NGH. The second part of the book is devoted to the new technical solutions adopted in DVB-NGH compared to DVB-T2. It also includes discussions between 3GPP and DVB to have a common standard--

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Record Nr.	UNINA9911006725003321
Autore	Riccio Michele
Titolo	Defects of Solid Semiconductor Structures
Pubbl/distr/stampa	Zurich : , : Trans Tech Publications, Limited, , 2024 ©2024
ISBN	9783036416359 3036416358
Edizione	[1st ed.]
Descrizione fisica	1 online resource (179 pages)
Collana	Defect and Diffusion Forum, , 1662-9507 ; ; Volume 434
Altri autori (Persone)	IraceAndrea BreglioGiovanni
Soggetti	Defects Silicon carbide
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia

Nota di contenuto	Intro -- Defects of Solid Semiconductor Structures -- Preface -- Table of Contents -- Evaluation of Basal Plane Dislocation Behavior near Epilayer and Substrate Interface -- Body Diode Reliability of 4H-SiC MOSFETs as a Function of Epitaxial Process Parameter -- Accuracy of EVC Method for the PiN Diode Pattern on SiC Epi-Wafer -- Study on Quantification of Correlation between Current Density and UV Irradiation Intensity, Leading to Bar Shaped 1SSF Expansion -- Early Detection of Bar-Shaped 1SSF before Expansion by PL Imaging -- Analysis of Forward Bias Degradation Reduction in 4H-SiC PiN Diodes on Bonded Substrates -- Investigation of Dislocation Behaviors in 4H-SiC Substrate during Post-Growth Thermal Treatment -- The Role of Defects on SiC Device Performance and Ways to Mitigate them -- Emission of Trapped Electrons from the 4H-SiC/SiO2-Interface via Photon-Irradiance at Cryogenic Temperatures -- SiC MOSFET Gate Oxide Quality Improvement Method in Furnace Thermal Oxidation with Lower Pressure Control -- Investigating Dislocation Arrays Induced by Seed Scratches during PVT 4H-SiC Crystal Growth Using Synchrotron X-Ray Topography -- Crystal Originated Defect Monitoring and Reduction in Production Grade SmartSiC™ Engineered Substrates -- Analysis of Lattice Damage in 4H-SiC Epiwafers Implanted with High Energy Al Ions at Elevated Temperatures -- Near-Interface Defect Decomposition during NO Annealing Analyzed by Molecular Dynamics Simulations -- Differences between Polar-Face and Non-Polar Face 4H-SiC/SiO2 Interfaces Revealed by Magnetic Resonance Spectroscopy -- Investigation of BPD Faulting under Extreme Carrier Injection in Room vs High Temperature Implanted 3.3kV SiC MOSFETs -- Epitaxial Defectivity Characterization Combining Surface Voltage and Photoluminescence Mapping on 200mm 4H-SiC Wafers. Buffer Layer Dependence of Defectivity in 200mm 4H-SiC Homoepitaxy -- A Study of Process Interruptions during Pre- and Post-Buffer Layer Epitaxial Growth for Defect Reduction in 4H SiC -- Practical Improvement of Noncontact Production Monitoring of Doping in SiC Wafers with Extended Epilayer Defects -- Analysis of Defect Structures during the Early-Stages of PVT Growth of 4H-SiC Crystals -- Development of 3-Channel Inspection Analysis Technique for Defects of SiC Epitaxial Wafers Using Optical Inspection, Photoluminescence and X-Ray Topography -- High-Volume SiC Epitaxial Layer Manufacturing-Maintaining High Materials Quality of Lab Results in Production -- Non-Destructive Quantification of In-Plane Depth Distribution of Sub-Surface Damage on 4H-SiC Wafers Using Laser Light Scattering -- Macro Step Bunching/Debunching Engineering on 4° off 4H-SiC (0001) to Control the BPD-TED Conversion Ratio by Dynamic AGE-Ing® -- Charge Carrier Capture by Prominent Defect Centers in 4H-SiC -- Keyword Index -- Author Index.
Sommario/riassunto	Special topic volume with invited peer-reviewed papers only.